







SN65220, SN65240, SN75240 SLLS266J - FEBRUARY 1997 - REVISED AUGUST 2022

# SNx52x0 USB Port Transient Suppressors

#### 1 Features

- Design to protect submicron 3-V or 5-V circuits from noise transients
- Port ESD protection capability exceeds:
  - 15-kV human body model
  - 2-kV machine model
- Available in a WCSP chip-scale package
- Stand-off voltage: 6 V (minimum)
- Low current leakage: 1-µA maximum at 6 V
- Low capacitance: 35-pF (typical)

### 2 Applications

- USB full-speed host, HUB, or peripheral
- Ports

### 3 Description

The SN65220 device is a dual, and the SN65240 and SN75240 devices are quadruple, unidirectional transient voltage suppressors (TVS). These devices provide electrical noise transient protection to Universal Serial Bus (USB) low and full-speed ports. The input capacitance of 35 pF makes it unsuitable for high-speed USB 2.0 applications.

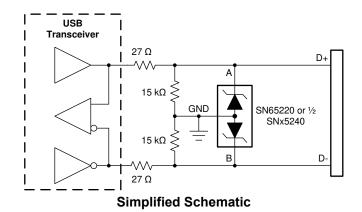
Any cabled I/O can be subjected to electrical noise transients from various sources. These noise transients can cause damage to the USB transceiver or the USB ASIC if they are of sufficient magnitude and duration.

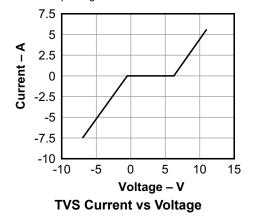
The SN65220, SN65240, and SN75240 devices ESD performance is measured at the system level, according to IEC61000-4-2; system design, however, impacts the results of these tests. To accomplish a high compliance level, careful board design and layout techniques are required.

#### Device Information<sup>(1)</sup>

| PART NUMBER | PACKAGE    | BODY SIZE (NOM)     |  |  |
|-------------|------------|---------------------|--|--|
| SN65220     | SOT-23 (6) | 2.90 mm × 1.60 mm   |  |  |
| 31103220    | DSBGA (4)  | 0.925 mm × 0.925 mm |  |  |
| SN65240     | PDIP (8)   | 9.09 mm × 6.35 mm   |  |  |
| SN75240     | TSSOP (8)  | 3.00 mm × 4.40 mm   |  |  |

See the orderable addendum at the end of the data sheet for all available packages.







### **Table of Contents**

| 1 Features  | 1  | 9.3 Feature Description  | 7                    |
|---|--|--|----------------------|
| 2 Applications  | 1  | 9.4 Device Functional Modes  | <mark>7</mark>       |
| 3 Description   | 1  | 10 Application and Implementation  | 8                    |
| 4 Revision History  |  | 10.1 Application Information   | <mark>8</mark>       |
| 5 Device Comparison Table   | 3  | 10.2 Typical Application   | <b>8</b>             |
| 6 Pin Configuration and Functions   | 3  | 11 Power Supply Recommendations  | 10                   |
| 7 Specifications  | 4  | 12 Layout  | 10                   |
| 7.1 Absolute Maximum Ratings  | 4  | 12.1 Layout Guidelines   | 10                   |
| 7.2 ESD Ratings   | 4  | 12.2 Layout Example  |                      |
| 7.3 Recommended Operating Conditions  | 4  | 13 Device and Documentation Support  |                      |
| 7.4 Thermal Information   |  | 13.1 Receiving Notification of Documentation Update  |                      |
| 7.5 Electrical Characteristics  | 4  | 13.2 Support Resources   |                      |
| 7.6 Typical Characteristics   |  | 13.3 Trademarks  |                      |
| 8 Parameter Measurement Information   |  | 13.4 Electrostatic Discharge Caution   |                      |
| 9 Detailed Description  |  | 13.5 Glossary  |                      |
| 9.1 Overview  |  | 14 Mechanical, Packaging, and Orderable  |                      |
| 9.2 Functional Block Diagram  | 6  | Information  | 11                   |
| NOTE: Page numbers for previous revisions r<br>Changes from Revision I (April 2021) to Re   | -  |  | Page                 |
|   |  | pressors in the <i>Device Comparison</i> table   |                      |
| Changes from Revision H (May 2015) to Re  | evision I (£   | April 2021)  | Page                 |
|   | , <b>v</b> 131011 1 ( <i>F</i>                             | (p. ii 202 i )   |                      |
| <ul> <li>Updated the numbering format for tables, t</li> </ul>  |  | · · · · ·  | 1                    |
|   | figures and  | cross-references throughout the document   |                      |
| • Updated the units for resistance from O to  | figures and $\Omega$ in the $Si$                           | cross-references throughout the documentimplified Schematic figure   | 1                    |
| <ul> <li>Updated the units for resistance from O to</li> <li>Updated the units from O to Ω in the <i>Typic</i></li> </ul>   | figures and<br>Ω in the Si<br>al Applicati                 | cross-references throughout the documentimplified Schematic figureion Schematic for ESD Protection of USB Transceiv  | 1<br>/ers            |
| <ul> <li>Updated the units for resistance from O to</li> <li>Updated the units from O to Ω in the <i>Typic</i> figure</li> </ul>  | figures and<br>Ω in the Si<br>al Applicati                 | cross-references throughout the documentimplified Schematic figure   | 1<br>/ers<br>8       |
| <ul> <li>Updated the units for resistance from O to</li> <li>Updated the units from O to Ω in the <i>Typic</i> figure</li> <li>Updated the units from O to Ω in the <i>Layon</i></li> </ul>                                     | figures and Ω in the Si al Applicati                       | cross-references throughout the documentimplified Schematic figureion Schematic for ESD Protection of USB Transcein of a 4-Layer Board With SN65220 figure | 1<br>/ers<br>8<br>10 |
| <ul> <li>Updated the units for resistance from O to</li> <li>Updated the units from O to Ω in the Typic figure</li> <li>Updated the units from O to Ω in the Layor</li> <li>Changes from Revision G (August 2008) to</li> </ul> | figures and Ω in the Si al Applicati  ut Example  Revision | cross-references throughout the documentimplified Schematic figureion Schematic for ESD Protection of USB Transcein of a 4-Layer Board With SN65220 figure | 1 /ers810 Page       |



# **5 Device Comparison Table**

| PRODUCT  | SUPPRESSORS | T <sub>A</sub> - RANGE | PACKAGE |
|----------|-------------|------------------------|---------|
| SN65220  | 2           | –40°C to 85°C          | WCSP-4  |
| 31103220 | 2           | _40 C to 65 C          | SOT23-6 |
| SN65240  | 4           | -40°C to 85°C          | DIP-8   |
| 31103240 |             | -40 C to 83 C          | TSSOP-8 |
| SN75240  | 4           | 0°C to 70°C            | DIP-8   |
| SN75240  | 4           | 0 0 10 70 0            | TSSOP-8 |

# **6 Pin Configuration and Functions**

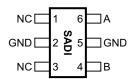




Figure 6-1. DBV Package, 6-Pin SOT-23 (Top View)

Figure 6-2. P, PW Package,s 8-Pin PDIP, TSSOP (Top View)

Table 6-1. Pin Functions

|      | PIN  |            | TYPE   | DESCRIPTION                         |  |
|------|------|------------|--|-------------------------------------|--|
| NAME | DBV  | P, PW      | 1175   | DESCRIPTION                         |  |
| Α    | 6    | 8          | Analog input                                     | Transient suppressor input – Line 1 |  |
| В    | 4    | 6          | Analog input                                     | Transient suppressor input – Line 2 |  |
| С    | _    | 2          | Analog input Transient suppressor input – Line 3 |                                     |  |
| D    | _    | 4          | Analog input                                     | Transient suppressor input – Line 4 |  |
| GND  | 2, 5 | 1, 3, 5, 7 | Power  | Local device ground                 |  |
| NC   | 1, 3 | _          | _  | Internally not connected            |  |

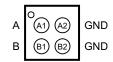


Figure 6-3. YZB Package, 4-Pin DSBGA (Top View)

### Table 6-2. Pin Functions

| PIN    | PIN TYPE |              | DESCRIPTION                         |
|--------|----------|--------------|-------------------------------------|
| NO.    | NAME     | IIFE         | DESCRIPTION                         |
| A1     | А        | Analog input | Transient suppressor input – Line 1 |
| B1     | В        | Analog input | Transient suppressor input – Line 2 |
| A2, B2 | GND      | Power        | Local device ground                 |



## 7 Specifications

### 7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

|                      |                            | MIN             | MAX | UNIT |
|----------------------|----------------------------|-----------------|-----|------|
| P <sub>D(peak)</sub> | Peak power dissipation     |                 | 60  | W    |
| I <sub>FSM</sub>     | Peak forward surge current |                 | 3   | Α    |
| I <sub>RSM</sub>     | Peak reverse surge current |                 | -9  | Α    |
| T <sub>stg</sub>     | Storage temperature        | <del>-</del> 65 | 150 | °C   |

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Section 7.3 is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

### 7.2 ESD Ratings

|                    |                         |  | VALUE  | UNIT |
|--------------------|-------------------------|--|--------|------|
|                    |                         | Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins <sup>(1)</sup>              | ±15000 |      |
| V <sub>(ESD)</sub> | Electrostatic discharge | Charged device model (CDM), per JEDEC specification JESD22-C101, all pins <sup>(2)</sup> | ±2000  | V    |

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 7.3 Recommended Operating Conditions

|     |                     |                  | MIN | MAX | UNIT |
|-----|---------------------|------------------|-----|-----|------|
| т.  | Ambient temperature | SN75240          | 0   | 70  | °C   |
| I A | Ambient temperature | SN65220, SN65240 | -40 | 85  |      |

#### 7.4 Thermal Information

|                        |  | SN65            | 5220           | SN65240,    | SN75240       |      |
|------------------------|--|-----------------|----------------|-------------|---------------|------|
|                        | THERMAL METRIC(1)                            | DBV<br>(SOT-23) | YZB<br>(DSBGA) | P<br>(PDIP) | PW<br>(TSSOP) | UNIT |
|                        |  | 6 PINS          | 4 BALLS        | 8 PINS      |               |      |
| $R_{\theta JA}$        | Junction-to-ambient thermal resistance       | 199.5           | 170            | 67.5        | 185.3         | °C/W |
| R <sub>0</sub> JC(top) | Junction-to-case (top) thermal resistance    | 159.7           | 1.8            | 57.9        | 68.8          | °C/W |
| $R_{\theta JB}$        | Junction-to-board thermal resistance         | 51.1            | 43.5           | 44.5        | 114.0         | °C/W |
| $\Psi_{JT}$            | Junction-to-top characterization parameter   | 41              | 9.2            | 36.2        | 9.9           | °C/W |
| ΨЈВ                    | Junction-to-board characterization parameter | 50.5            | 43.5           | 44.5        | 112.3         | °C/W |

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

### 7.5 Electrical Characteristics

over recommended operating conditions (unless otherwise noted)

|                   | PARAMETER                   | TEST CONDITIONS                                  | MIN | TYP | MAX | UNIT |
|-------------------|-----------------------------|--|-----|-----|-----|------|
| I <sub>lkg</sub>  | Leakage current             | V <sub>I</sub> = 6 V at A, B, C, or D terminals  |     |     | 1   | μΑ   |
| V <sub>(BR)</sub> | Breakdown voltage           | V <sub>I</sub> = 1 mA at A, B, C, or D terminals | 6.5 | 7   | 8   | V    |
| C <sub>IN</sub>   | Input capacitance to ground | V <sub>I</sub> = 0.4 sin (4E6πt) + 0.5 V         |     | 35  |     | pF   |

Submit Document Feedback



# 7.6 Typical Characteristics

 $T_A = 25$ °C unless otherwise noted.

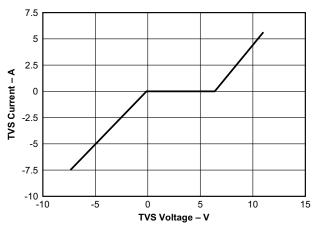


Figure 7-1. Transient-Voltage-Suppressor Current vs Voltage

### **8 Parameter Measurement Information**

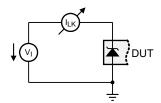


Figure 8-1. Measurement of Leakage Current

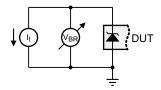


Figure 8-2. Measurement of Breakdown Voltage

### 9 Detailed Description

### 9.1 Overview

The SN65220, SN65240, and SN75240 devices integrate multiple unidirectional transient voltage suppressors (TVS). Figure 9-1 shows the equivalent circuit diagram of a single TVS diode.

For positive transient voltages, only the Q1 transistor determines the switching characteristic. When the input voltage reaches the Zener voltage,  $V_Z$ , Zener diode D1 conducts; therefore, allowing for the base-emitter voltage,  $V_{BE}$ , to increase. At  $V_{IN} = V_Z + V_{BE}$ , the transistor starts conducting. From then on, its on-resistance decreases linearly with increasing input voltage.

For negative transient voltages, only diode D2 determines the switching characteristic. Here, switching occurs when the input voltage exceeds the diode forward voltage,  $V_{FW}$ .

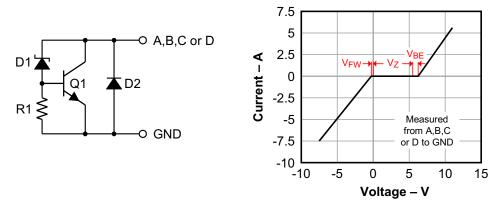
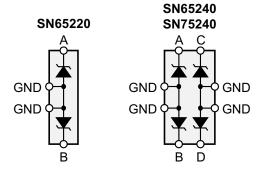


Figure 9-1. TVS Structure and Current — Voltage Characteristic

### 9.2 Functional Block Diagram





### 9.3 Feature Description

The SN65220, SN65240, and SN75240 family of unidirectional transient voltage suppressors provide transient protection to Universal Serial Bus low and full-speed ports. These TVS diodes provide a minimum breakdown voltage of 6.5-V to protect USB transceivers and USB ASICs typically implemented in 3-V or 5-V digital CMOS technology.

### 9.4 Device Functional Modes

TVS diodes possess two functional modes, a high-impedance and a conducting mode.

During normal operating conditions, that is in the absence of high voltage transients, the breakdown voltage of TVS diodes is not exceeded and the devices remain high-impedance.

In the presence of high-voltage transients the breakdown voltage is exceeded. The TVS diodes then conduct and become low-impedance. In this mode excessive transient energy is shunted directly to local circuit ground, preventing USB transceivers from electrical damage.

## 10 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

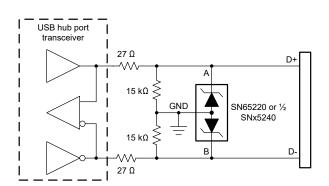
### 10.1 Application Information

The USB has become a popular solution to connect PC peripherals. The USB allows devices to be hot-plugged in and out of the existing PC system without rebooting or turning off the PC. Because frequent human interaction with the USB system occurs as a result of its attractive hot-plugging ability, there is the possibility for large ESD strikes and damage to crucial system elements. The ESD protection included on the existing hardware is typically in the 2-kV to 4-kV range for the human body model (HBD) and 200-V to 300-V for the machine model (MM). The ESD voltage levels found in a normal USB operating environment can exceed these levels. The SN75240, SN65240, and SN65220 devices will increase the robustness of the existing USB hardware to ESD strikes common to the environment in which USB is likely to be used.

#### **10.2 Typical Application**

Figure 10-1 shows a typical USB system and application of the SN75240, SN65240, and SN65220 devices. Connections to pin A from the D+ data line, pin B from the D– data line, and the device grounds from the GND line that already exists are necessary to increase the amount of ESD protection provided to the USB port.

The design of the suppressor gives it very low maximum current leakage of 1  $\mu$ A, a very low typical capacitance of 35 pF, and a standoff voltage minimum of 6 V. Because of these levels, the SN75240, SN65240, and SN65220 devices will provide added protection to the USB system hardware during ESD events without introducing the high capacitance and current leakage levels typical of external transient voltage suppressors. The addition of an SN75240, SN65240, or SN65220 device is beneficial to both full-speed and low-speed USB 1.1 bandwidth standards.



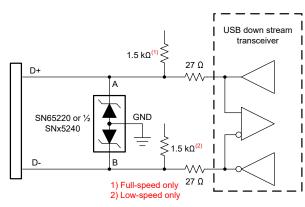


Figure 10-1. Typical Application Schematic for ESD Protection of USB Transceivers



### 10.2.1 Design Requirements

For this design example, use the parameters listed in Table 10-1 as design parameters.

**Table 10-1. Design Parameters** 

| DESIGN PARAMETER                         | EXAMPLE VALUE |
|--|---------------|
| Minimum breakdown voltage (TVS)          | 6.5 V         |
| Maximum supply voltage (USB transceiver) | 5.5 V         |
| Typical junction capacitance (TVS)       | 35 pF         |
| Maximum data rate (USB transceiver)      | 12 Mbps       |

### 10.2.2 Detailed Design Procedure

To effectively protect USB transceivers, use TVS diodes with breakdown voltages close to 6 V, such as the SN65220, SN65240, or SN75220 devices.

Because of the TVS junction capacitance of 35 pF, apply these TVS diodes only to USB transceivers with full-speed capability that is 12 Mbps maximum.

Place the TVS diodes as close to the board connector as possible to prevent transient energies from entering further board space.

Connect the TVS diode between the data lines (D+, D–) and local circuit ground (GND).

Because noise transient represents high-speed frequencies, ensure low-inductance return paths for the transient currents by providing a solid ground plane and using two VIAs connecting the TVS terminals to ground.

### 10.2.3 Application Curve

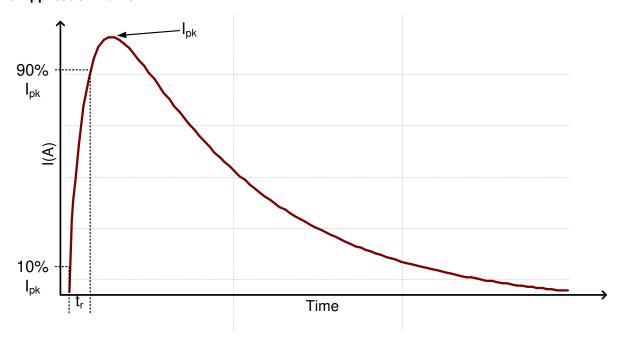


Figure 10-2. HBM Curve

## 11 Power Supply Recommendations

Unlike other semiconductor components that require a supply voltage to operate, the SN65220, SN65240, and SN75240 transient suppressors are combinations of multiple p-n diodes, activated by transient voltages. Therefore, these transient suppressors do not require external voltage supplies.

## 12 Layout

### 12.1 Layout Guidelines

The multiple ground pins provided lower the connection resistance to ground. In order to improve circuit operation, a connection to all ground pins must be provided on the system printed circuit board. Without proper device connection to ground, the speed and protection capability of the device will be degraded.

- The ground termination pads should be connected directly to a ground plane on the board for optimum performance. A single trace ground conductor will not provide an effective path for fast rise-time transient events including ESD due to parasitic inductance.
- Nominal inductive values of a PCB trace are approximately 20 nH/cm. This value may seem small, but an
  apparent short length of trace may be sufficient to produce significant L(di/dt) effects with fast rise-time ESD
  spikes.
- Mount the TVS as close as possible to the I/O socket to reduce radiation originating from the transient as it is
  routed to ground.

#### Note

Direct connective paths of the traces are taken to the suppressor mounting pads to minimize parasitic inductance in the surge-current conductive path, thus minimizing L(di/dt) effects.

### 12.2 Layout Example

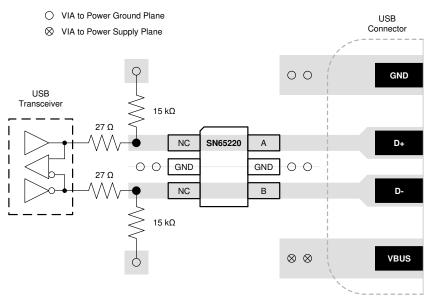


Figure 12-1. Layout Example of a 4-Layer Board With SN65220



### 13 Device and Documentation Support

### 13.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 13.2 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 13.3 Trademarks

TI E2E<sup>™</sup> is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

### 13.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 13.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

## 14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 23-May-2025

#### PACKAGING INFORMATION

| Orderable part number | Status   | Material type | Package   Pins   | Package qty   Carrier | RoHS | Lead finish/  | MSL rating/        | Op temp (°C) | Part marking |
|-----------------------|----------|---------------|------------------|-----------------------|------|---------------|--------------------|--------------|--------------|
|                       | (1)      | (2)           |                  |                       | (3)  | Ball material | Peak reflow        |              | (6)          |
|                       |          |               |                  |                       |      | (4)           | (5)                |              |              |
| SN65220DBVR           | Active   | Production    | SOT-23 (DBV)   6 | 3000   LARGE T&R      | Yes  | NIPDAU        | Level-1-260C-UNLIM | -40 to 85    | SADI         |
| SN65220DBVR.A         | Active   | Production    | SOT-23 (DBV)   6 | 3000   LARGE T&R      | Yes  | NIPDAU        | Level-1-260C-UNLIM | -40 to 85    | SADI         |
| SN65220DBVRG4         | Active   | Production    | SOT-23 (DBV)   6 | 3000   LARGE T&R      | -    | Call TI       | Call TI            | -40 to 85    |              |
| SN65220DBVT           | Obsolete | Production    | SOT-23 (DBV)   6 | -                     | -    | Call TI       | Call TI            | -40 to 85    | SADI         |
| SN65240P              | Active   | Production    | PDIP (P)   8     | 50   TUBE             | Yes  | NIPDAU        | N/A for Pkg Type   | -40 to 85    | SN65240P     |
| SN65240P.A            | Active   | Production    | PDIP (P)   8     | 50   TUBE             | Yes  | NIPDAU        | N/A for Pkg Type   | -40 to 85    | SN65240P     |
| SN65240PW             | Obsolete | Production    | TSSOP (PW)   8   | -                     | -    | Call TI       | Call TI            | -40 to 85    | A65240       |
| SN65240PWR            | Active   | Production    | TSSOP (PW)   8   | 2000   LARGE T&R      | Yes  | NIPDAU        | Level-1-260C-UNLIM | -40 to 85    | A65240       |
| SN65240PWR.A          | Active   | Production    | TSSOP (PW)   8   | 2000   LARGE T&R      | Yes  | NIPDAU        | Level-1-260C-UNLIM | -40 to 85    | A65240       |
| SN75240P              | Active   | Production    | PDIP (P)   8     | 50   TUBE             | Yes  | NIPDAU        | N/A for Pkg Type   | 0 to 70      | SN75240P     |
| SN75240P.A            | Active   | Production    | PDIP (P)   8     | 50   TUBE             | Yes  | NIPDAU        | N/A for Pkg Type   | 0 to 70      | SN75240P     |
| SN75240PW             | Obsolete | Production    | TSSOP (PW)   8   | -                     | -    | Call TI       | Call TI            | 0 to 70      | A75240       |

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

## PACKAGE OPTION ADDENDUM

www.ti.com 23-May-2025

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

#### OTHER QUALIFIED VERSIONS OF SN65220:

Automotive: SN65220-Q1

NOTE: Qualified Version Definitions:

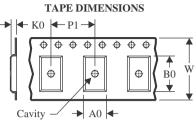
Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

# **PACKAGE MATERIALS INFORMATION**

www.ti.com 23-May-2025

### TAPE AND REEL INFORMATION





| A0 | Dimension designed to accommodate the component width     |
|----|---|
| В0 | Dimension designed to accommodate the component length    |
| K0 | Dimension designed to accommodate the component thickness |
| W  | Overall width of the carrier tape                         |
| P1 | Pitch between successive cavity centers                   |

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

| Device      | Package<br>Type | Package<br>Drawing |   | SPQ  | Reel<br>Diameter<br>(mm) | Reel<br>Width<br>W1 (mm) | A0<br>(mm) | B0<br>(mm) | K0<br>(mm) | P1<br>(mm) | W<br>(mm) | Pin1<br>Quadrant |
|-------------|-----------------|--------------------|---|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| SN65220DBVR | SOT-23          | DBV                | 6 | 3000 | 178.0                    | 9.0                      | 3.23       | 3.17       | 1.37       | 4.0        | 8.0       | Q3               |
| SN65240PWR  | TSSOP           | PW                 | 8 | 2000 | 330.0                    | 12.4                     | 7.0        | 3.6        | 1.6        | 8.0        | 12.0      | Q1               |

www.ti.com 23-May-2025



### \*All dimensions are nominal

| Device      | Package Type | Package Drawing | Pins | SPQ  | Length (mm) | Width (mm) | Height (mm) |
|-------------|--------------|-----------------|------|------|-------------|------------|-------------|
| SN65220DBVR | SOT-23       | DBV             | 6    | 3000 | 180.0       | 180.0      | 18.0        |
| SN65240PWR  | TSSOP        | PW              | 8    | 2000 | 356.0       | 356.0      | 35.0        |

# **PACKAGE MATERIALS INFORMATION**

www.ti.com 23-May-2025

### **TUBE**



\*All dimensions are nominal

| Device     | Package Name | Package Type | Pins | SPQ | L (mm) | W (mm) | T (µm) | B (mm) |
|------------|--------------|--------------|------|-----|--------|--------|--------|--------|
| SN65240P   | Р            | PDIP         | 8    | 50  | 506    | 13.97  | 11230  | 4.32   |
| SN65240P.A | Р            | PDIP         | 8    | 50  | 506    | 13.97  | 11230  | 4.32   |
| SN75240P   | Р            | PDIP         | 8    | 50  | 506    | 13.97  | 11230  | 4.32   |
| SN75240P.A | Р            | PDIP         | 8    | 50  | 506    | 13.97  | 11230  | 4.32   |

# P (R-PDIP-T8)

# PLASTIC DUAL-IN-LINE PACKAGE



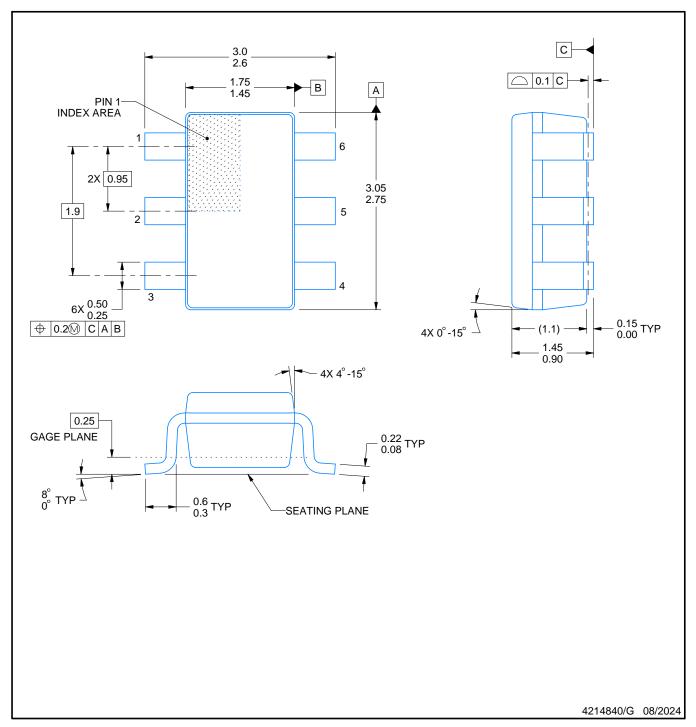
NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.





SMALL OUTLINE TRANSISTOR



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

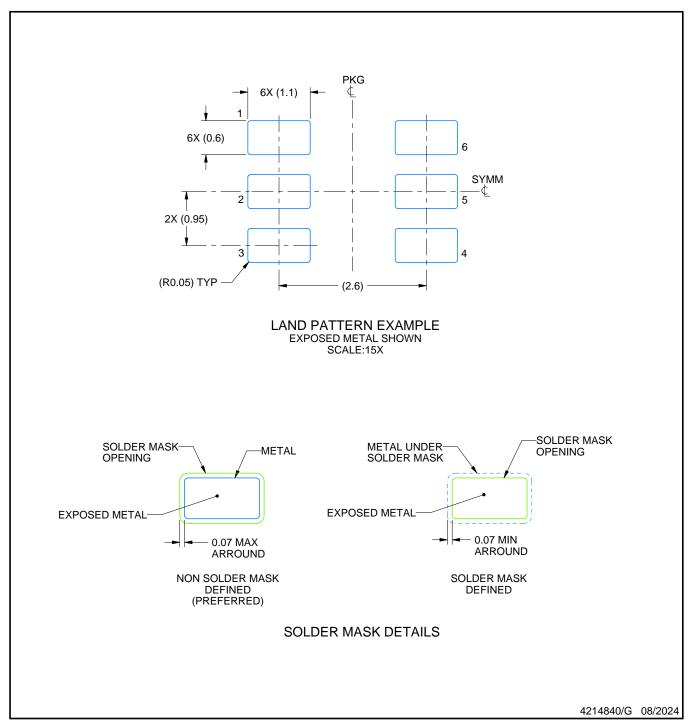
  2. This drawing is subject to change without notice.

  3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.

- 4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- 5. Refernce JEDEC MO-178.



SMALL OUTLINE TRANSISTOR



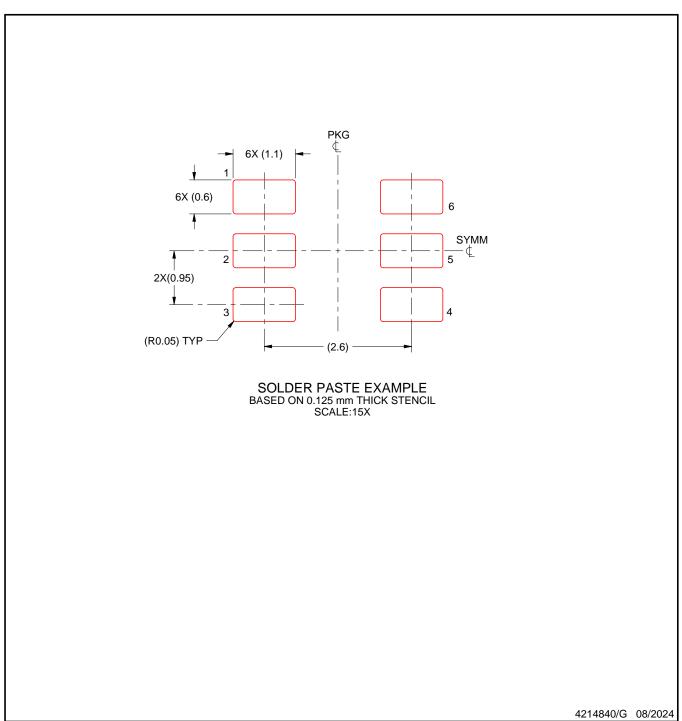
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



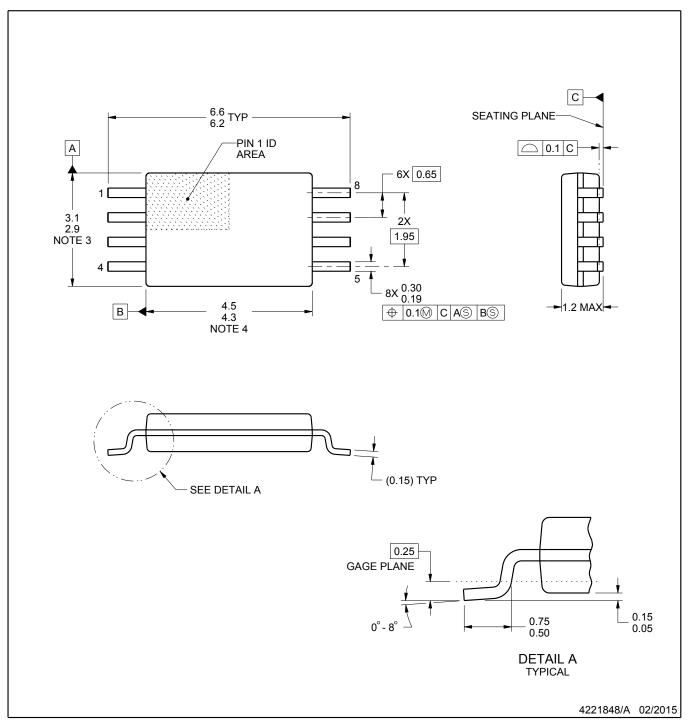
NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE PACKAGE



### NOTES:

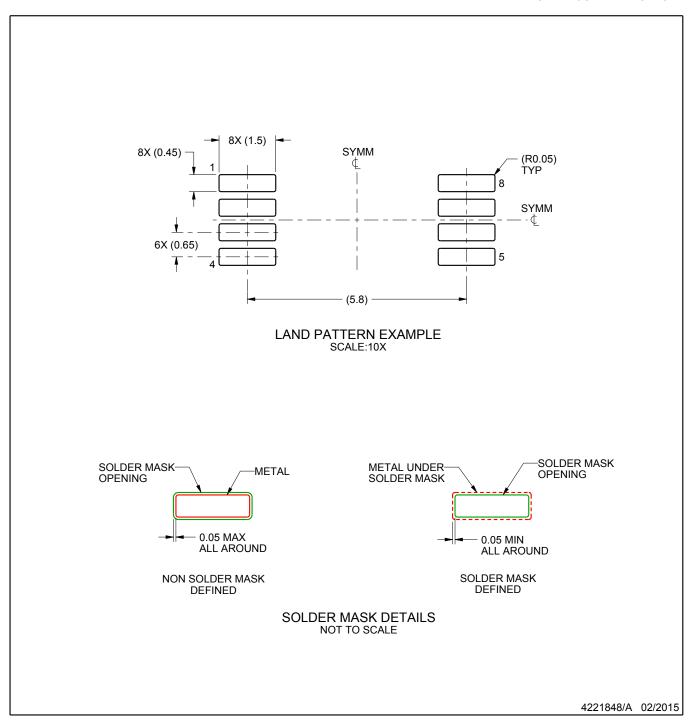
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153, variation AA.



SMALL OUTLINE PACKAGE



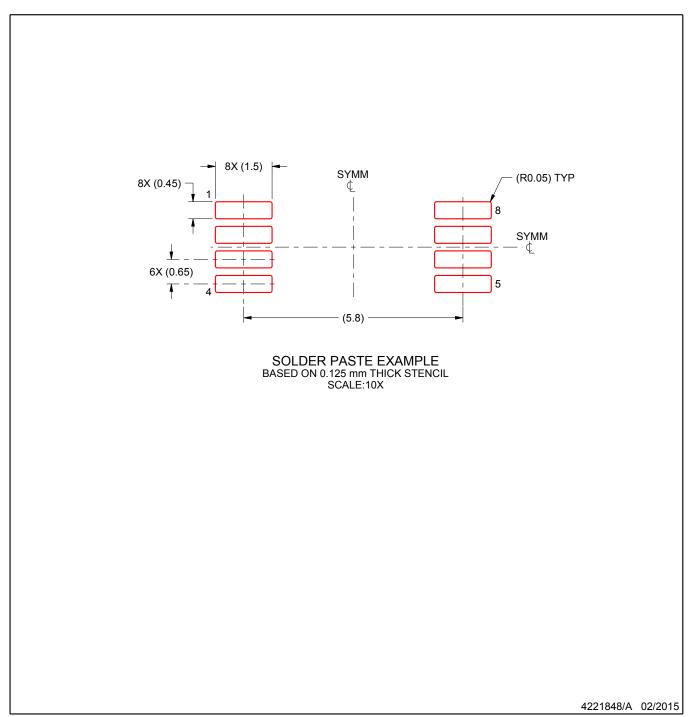
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



### IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2025. Texas Instruments Incorporated